Pontifícia Universidade Católica
do Rio de Janeiro

Fernando Henrique do Rêgo Monteiro

A study on the production and characterization of boron doped single wall carbon nanotubes

Dissertação de Mestrado

Thesis presented to the Programa de Pós-graduação em Física of the Departamento de Física, PUC-Rio as partial fulfillment of the requirements for the degree of Mestre em Física

Advisor: Prof. Fernando Lázaro Freire Jr.

Rio de Janeiro
March 2012

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Received bachelor degree in Physics from Pontifícia Universidade Católica do Rio de Janeiro - PUC-Rio in 2009.

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Bibliographic data

Rêgo Monteiro, Fernando Henrique

A study on the production and characterization of boron doped single wall carbon nanotubes / Fernando Henrique do Rêgo Monteiro ; advisor: Fernando Lázaro Freire Jr.. — 2012.
74 f. : il. ; 30 cm

Dissertação (Mestrado em Física)-Pontifícia Universidade Católica do Rio de Janeiro, Rio de Janeiro, 2012.
Inclui bibliografia

1. Física – Teses. 2. Nanotubos de carbono; Boro; CVD; Raman; XPS. I. Freire Jr., Fernando Lázaro. II. Pontifícia Universidade Católica do Rio de Janeiro. Departamento de Física. III. Título.

CDD: 530

Acknowledgments

To God.

To my parents and brother.

To professor Fernando Lázaro Freire Jr, by accepting me for this work, always providing the best research conditions, guidance, discussions, by listening to all my doubts and helping me with them and by the friendship.

To professor Marcelo Eduardo Huguenin Maia da Costa, who helped me a lot in almost everything, including XPS measurements and analysis, Raman measurements, LATEX, many other things that I can not remember now and by the friendship.

To Dunieskys Roberto Gonzáles Larrudé who helped me with discussions, by being the one who had taken the TEM images of this work, for being the one with the greatest contribution on the assembly of the CVD system used on this work and by the friendship.

To my girlfriend Paula Alvarez who always supported and helped me in everything that I need, stayed at my side in every moment, by a little help with LATEX and the grammar corrections of this work.

To Thiago Guerreiro, with whom I had several discussions in almost everything (that is nice) in physics, by the support along this work and by the friendship.

To Erick Costa e Silva Talarico, by the support, discussions, by the great help on the assembly of the first prototype of the CVD system, and by the friendship.

To Fábio Alex Pereira dos Santos, by the several discussions and friendship.

To Carlos Augusto de Oliveira, by all good ideas regarding the CVD system and the friendship.

To Cássia Ribeiro Ponciano, Edson Joaquim, Nilton Cesar Ferreira Gomes, Sérgio Martins Xavier, Gizelda Dias da Silva and all PUC-Rio staff.

To the professors Hiroshi Nunokawa, Welles Antônio Martinez Morgado, Vera Lúcia Vieira Baltar and André Silva Pimentel, by several discussions and friendship.

To all my friends and colleagues who directly or not contributed or supported me on this work.

To PUC-Rio, FAPERJ and CNPq by all the financial support.

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Abstract

Rêgo Monteiro, Fernando Henrique; Freire Jr., Fernando Lázaro. **A study on the production and characterization of boron doped single wall carbon nanotubes**. Rio de Janeiro, 2012. 74p. Dissertação de Mestrado — Departamento de Física, Pontifícia Universidade Católica do Rio de Janeiro.

We studied in this work the synthesis and characterization of boron doped single wall carbon nanotubes. They were produced, at different conditions, using a new liquid precursor in a high vacuum chemical vapour deposition system. In order to characterize the samples we compared them to an undoped reference sample and used a transmission and field emission scanning electron microscopy, Raman spectroscopy and a X-ray photoemission spectroscopy (XPS). The transmission electron microscopy and the Raman spectroscopy were used to confirm the presence of single wall carbon nanotubes, while the scanning electron microscopy was used to identify in which temperature range the tubes were produced. We found evidences that the produced sample were doped by comparing the Raman spectra of the samples with the reference one. By using the XPS, we could determine that our tubes are boron doped. By comparing the Raman analysis with the XPS results, we developed a simple rule to estimate the doping level through Raman measurements.

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Keywords

SWNT; Boron; High Vacuum CVD; Raman spectroscopy; XPS.

Resumo

Rêgo Monteiro, Fernando Henrique; Freire Jr., Fernando Lázaro. **Produção e caracterização de nanotubos de carbono de parede simples dopados com boro**. Rio de Janeiro, 2012. 74p. Dissertação de Mestrado — Departamento de Física, Pontifícia Universidade Católica do Rio de Janeiro.

Neste trabalho estudamos a síntese e caracterização de nanotubos de carbono de parede simples dopados com boro, que foram produzidos em diferentes condições, usando um precursor líquido em um sistema CVD de alto vácuo. Para a caracterização comparamos as amostras com outras − de referência sem dopagem − e também usamos microscópios de transmissão e varredura, espectroscopia Raman e espectroscopia por fotoelétrons excitados por raio X (XPS). A microscopia de transmissão e a espectroscopia Raman foram usadas para confirmar a presença de nanotubos de parede simples, enquanto a microscopia de varredura foi usada para identificar em qual faixa de temperatura os nanotubos foram produzidos. Achamos evidências de que as amostras estão dopadas ao compararmos os espectros Raman dos nanotubos com as amostras de referência. Usando os resultados do XPS, determinamos que os nossos tubos estão dopados com boro. Comparando a análise Raman com esses resultados, desenvolvemos uma regra simples para estimar o nível de dopagem a partir de medidas Raman.

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Palavras–chave

Nanotubos de carbono; Boro; CVD; Raman; XPS.

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"– Data, find a way to defeat that shield.
– That may be impossible, sir.
– Things are only impossible until they're not.
– Yes, sir."

Picard and Data, *Star Trek, TNG.*